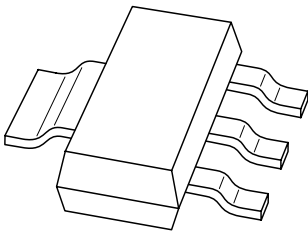


DATA SHEET



PZTA92 PNP high-voltage transistor

Product specification
Supersedes data of 1997 May 22

1999 Apr 14

PNP high-voltage transistor

PZTA92

FEATURES

- Low current (max. 100 mA)
- High voltage (max. 300 V).

APPLICATIONS

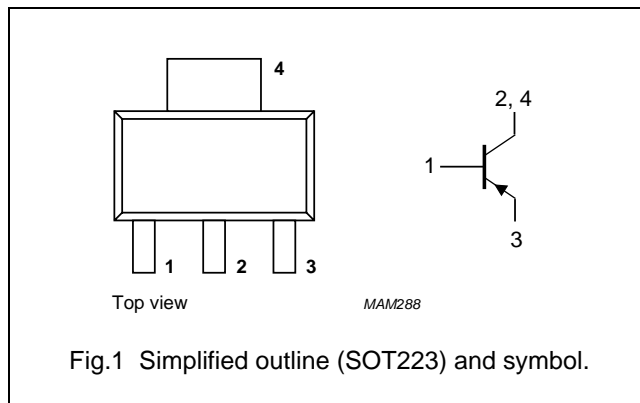
- Video equipment
- Telephony
- Professional communication equipment.

DESCRIPTION

PNP high-voltage transistor in a SOT223 plastic package.
NPN complement: PZTA42.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–300	V
V_{CEO}	collector-emitter voltage	open base	–	–300	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1	–	1.2	W
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	104	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		23	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -200\text{ V}$	–	–20	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{BE} = -5\text{ V}$	–	–100	nA
h_{FE}	DC current gain	$I_C = -1\text{ mA}; V_{CE} = -10\text{ V}; \text{note 1}$	25	–	
		$I_C = -10\text{ mA}; V_{CE} = -10\text{ V}; \text{note 1}$	40	–	
		$I_C = -30\text{ mA}; V_{CE} = -10\text{ V}; \text{note 1}$	25	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -20\text{ mA}; I_B = -2\text{ mA}$	–	–500	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -20\text{ mA}; I_B = -2\text{ mA}$	–	–900	mV
C_c	collector capacitance	$I_E = 0; V_{CB} = -20\text{ V}; f = 1\text{ MHz}$	–	6	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	50	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

PNP high-voltage transistor

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223

